L Number	Hits	Search Text	DB	Time stamp
3	4237	(laser near3 ablat$3) same (via hole open$4 trench contact)	USPAT; US-PGPUB	2004/06/08 14:35
4	107	((laser near3 ablat$3) same (via hole open$4 trench contact)) and (TFT (thin near5 film near5 transistor))	USPAT; US-PGPUB	2004/06/08 14:35
5	1392	((laser near3 ablat$3) same (via hole open$4 trench contact)) and isolat$3	USPAT; US-PGPUB	2004/06/08 14:34
6	155	(((laser near3 ablat$3) same (via hole open$4 trench contact)) and isolat$3) and (device near5 isolat$3)	USPAT; US-PGPUB	2004/06/08 14:34
7	5	(((laser near3 ablat$3) same (via hole open$4 trench contact)) and (TFT (thin near5 film near5 transistor))) and ((((laser near3 ablat$3) same (via hole open$4 trench contact)) and isolat$3) and (device near5 isolat$3))	USPAT; US-PGPUB	2004/06/08 14:34
8	350	(laser near3 ablat$3) same (via hole open$4 trench contact)	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 14:35
9	531	(laser near3 ablat$3) and (via hole open$4 trench contact)	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 14:35
10	531	((laser near3 ablat$3) same (via hole open$4 trench contact)) ((laser near3 ablat$3) and (via hole open$4 trench contact))	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 14:35
11	1	(((laser near3 ablat$3) same (via hole open$4 trench contact)) ((laser near3 ablat$3) and (via hole open$4 trench contact))) and (TFT (thin near5 film near5 transistor))	EPO; JPO; DERWENT; IBM_TDB	2004/06/08 14:35
-	28052	(TFT (thin near5 film near5 transistor))	USPAT; US-PGPUB	2004/06/08 14:33
-	1898	((TFT (thin near5 film near5 transistor))) and (solution near10 process$3)	USPAT; US-PGPUB	2004/05/24 11:31
-	1592	(((TFT (thin near5 film near5 transistor))) and (solution near10 process$3)) and pattern$4	USPAT; US-PGPUB	2004/05/24 11:32
-	799	((((TFT (thin near5 film near5 transistor))) and (solution near10 process$3)) and pattern$4) and (dielectric inuslat$3)	USPAT; US-PGPUB	2004/05/24 11:21
-	24	(((((TFT (thin near5 film near5 transistor))) and (solution near10 process$3)) and pattern$4) and (dielectric inuslat$3)) and (laser near5 ablat$3)	USPAT; US-PGPUB	2004/05/24 11:32
-	14	((((((TFT (thin near5 film near5 transistor))) and (solution near10 process$3)) and pattern$4) and (dielectric inuslat$3)) and (laser near5 ablat$3)) and (spin near5 coat$3)	USPAT; US-PGPUB	2004/05/24 11:28
-	31941	ink near5 jet near5 print$3	USPAT; US-PGPUB	2004/05/24 11:34
-	1378	(ink near5 jet near5 print$3) and (source and drain)	USPAT; US-PGPUB	2004/05/24 11:34
-	491	((ink near5 jet near5 print$3) and (source and drain)) and (TFT (thin near5 film near5 transistor))	USPAT; US-PGPUB	2004/05/24 11:29
-	40	(((ink near5 jet near5 print$3) and (source and drain)) and (TFT (thin near5 film near5 transistor))) and (laser near5 ablat$3)	USPAT; US-PGPUB	2004/05/24 11:29
-	36555	(TFT (thin near5 film near5 transistor))	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:31
-	1715	((TFT (thin near5 film near5 transistor))) and (solution and process$3)	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:32
-	454	(((TFT (thin near5 film near5 transistor))) and (solution and process$3)) and pattern$4	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:32
-	36	((((TFT (thin near5 film near5 transistor))) and (solution and process$3)) and pattern$4) and (laser ablat$3)	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:33

-	34570	ink near5 jet near5 print$3	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:34
-	32	(ink near5 jet near5 print$3) and (source and drain)	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 11:35
-	816918	print$3 writ$3	USPAT; US-PGPUB	2004/05/24 12:27
-	13221	(print$3 writ$3) and (TFT (thin near5 film near5 transistor))	USPAT; US-PGPUB	2004/05/24 12:28
-	7402	((print$3 writ$3) and (TFT (thin near5 film near5 transistor))) and (laser near$5 ablat$3)	USPAT; US-PGPUB	2004/05/24 12:28
-	4333	(((print$3 writ$3) and (TFT (thin near5 film near5 transistor))) and (laser near$5 ablat$3)) and (source and drain)	USPAT; US-PGPUB	2004/05/24 12:07
-	4277	((((print$3 writ$3) and (TFT (thin near5 film near5 transistor))) and (laser near$5 ablat$3)) and (source and drain)) and gate	USPAT; US-PGPUB	2004/05/24 12:07
-	498	(((((print$3 writ$3) and (TFT (thin near5 film near5 transistor))) and (laser near$5 ablat$3)) and (source and drain)) and gate) and (ink near5 jet)	USPAT; US-PGPUB	2004/05/24 12:07
-	485	((((((print$3 writ$3) and (TFT (thin near5 film near5 transistor))) and (laser near$5 ablat$3)) and (source and drain)) and gate) and (ink near5 jet)) and pattern$4	USPAT; US-PGPUB	2004/05/24 12:08
-	1218286	print$3 writ$3	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:28
-	1324	(print$3 writ$3) and (TFT (thin near5 film near5 transistor))	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:28
-	77	((print$3 writ$3) and (TFT (thin near5 film near5 transistor))) and (laser near$5 ablat$3)	EPO; JPO; DERWENT; IBM_TDB	2004/05/24 12:28
-	28319	(TFT (thin near5 film near5 transistor))	USPAT; US-PGPUB	2004/06/07 12:23
-	441	((TFT (thin near5 film near5 transistor))) and (laser near5 ablat$6)	USPAT; US-PGPUB	2004/06/07 12:24
-	68	(((TFT (thin near5 film near5 transistor))) and (laser near5 ablat$6)) and isolation	USPAT; US-PGPUB	2004/06/07 12:42
-	4702	(laser near5 ablat$3) same (pattern$4 etch$3)	USPAT; US-PGPUB	2004/06/07 12:43
-	235	((TFT (thin near5 film near5 transistor))) and ((laser near5 ablat$3) same (pattern$4 etch$3))	USPAT; US-PGPUB	2004/06/07 14:40
-	0	((channel near3 length) with ("5" adj3 micoron))	USPAT; US-PGPUB	2004/06/07 15:31
-	1	("6602790").PN.	USPAT; US-PGPUB	2004/06/07 19:58
-	28319	(TFT (thin near5 film near5 transistor))	USPAT; US-PGPUB	2004/06/07 19:59
-	415	((TFT (thin near5 film near5 transistor))) and (laser near3 ablat$3)	USPAT; US-PGPUB	2004/06/07 20:24
-	178	(((TFT (thin near5 film near5 transistor))) and (laser near3 ablat$3)) and (STI isolat$3)	USPAT; US-PGPUB	2004/06/07 20:00
-	3559	(laser near3 ablat$3) same (via hole trench open$3 groove recess)	USPAT; US-PGPUB	2004/06/07 20:24
-	2240	(laser near3 ablat$3) with (via hole trench open$3 groove recess)	USPAT; US-PGPUB	2004/06/07 20:25
-	797	((laser near3 ablat$3) with (via hole trench open$3 groove recess)) and isolat$3	USPAT; US-PGPUB	2004/06/07 20:25
-	517	(((laser near3 ablat$3) with (via hole trench open$3 groove recess)) and isolat$3) and (print$3 writ$3 inkjet ink-jet)	USPAT; US-PGPUB	2004/06/07 20:44
-	2	(device near3 isolat$3) near20 (laser near5 ablat$3)	USPAT; US-PGPUB	2004/06/07 20:44